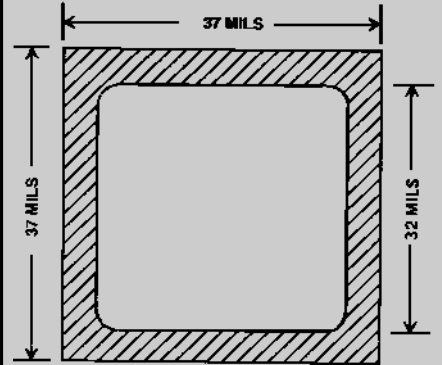


- 1N5819 AND 1N6761 AVAILABLE IN JANHC AND JANKC PER MIL PRF-19500/586
- 1 AMP SCHOTTKY BARRIER RECTIFIER CHIPS
- SILICON DIOXIDE PASSIVATED
- COMPATIBLE WITH ALL WIRE BONDING AND DIE ATTACH TECHNIQUES, WITH THE EXCEPTION OF SOLDER REFLOW

CD5817 thru CD5819
and
CD6759 thru CD6761
and
CD1A20 thru CD1A100

MAXIMUM RATINGS

Operating Temperature: -55°C to +125°C
Storage Temperature: -55°C to +150°C
Average Rectified Forward Current: 1.0 AMP @ +55°C
Derating: 14.3 mA / °C above +55°C



BACKSIDE IS CATHODE
FIGURE 1

CDI TYPE NUMBER	WORKING PEAK REVERSE VOLTAGE	MAXIMUM FORWARD VOLTAGE		MAXIMUM REVERSE LEAKAGE CURRENT AT RATED VOLTAGE	
	V _{RWM}	V _{F@0.1A}	V _{F@1.0A}	I _{R@25°C}	I _{R@100°C}
	VOLTS	VOLTS	VOLTS	mA	mA
CD5817	20	0.36	0.60	0.10	5.0
CD5818	30	0.36	0.60	0.10	5.0
CD5819	40	0.36	0.60	0.10	5.0
JHC, JKC 5819	45	0.34	0.49	0.05	5.0
CD6759	60	0.38	0.75	0.10	6.0
CD6760	80	0.38	0.75	0.10	6.0
CD6761	100	0.38	0.75	0.10	6.0
JHC, JKC 6761	100	0.38	0.69	0.10	12.0
CD1A20	20	0.36	0.60	0.10	5.0
CD1A30	30	0.36	0.60	0.10	5.0
CD1A40	40	0.36	0.60	0.10	5.0
CD1A50	50	0.36	0.60	0.10	5.0
CD1A60	60	0.38	0.75	0.10	12.0
CD1A80	80	0.38	0.75	0.10	12.0
CD1A100	100	0.38	0.75	0.10	12.0

DESIGN DATA

METALLIZATION:
Top: (Anode)Al
Back: (Cathode)Au

AL THICKNESS.....25,000 Å Min
GOLD THICKNESS.....4,000 Å Min
CHIP THICKNESS.....10 MILS

TOLERANCES: ALL
Dimensions ± 2 mils



CD5817 thru CD5819 and CD6759 thru CD6761 and CD1A20 thru CD1A100

TYPICAL REVERSE LEAKAGE CURRENT AT RATED PIV (PULSED)

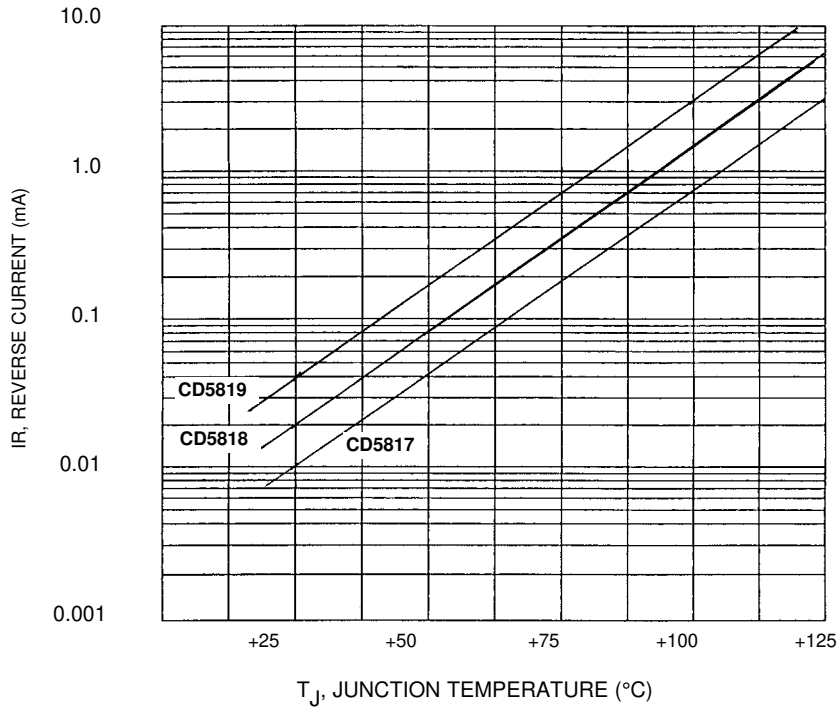


FIGURE 1

TYPICAL FORWARD VOLTAGE

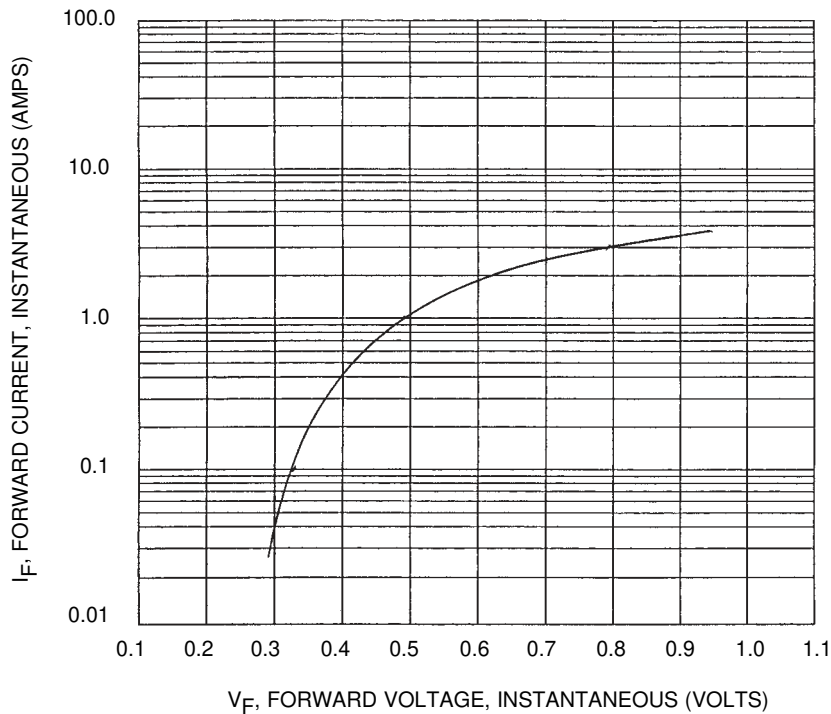


FIGURE 2